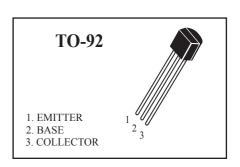




### **NPN General Purpose Transistors**



DataSheet4U.com



#### ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

| Rating   | Symbol           | Value       | Unit |
|--|------------------|-------------|------|
| Collector-Emitter Voltage                      | VCEO             | 45          | Vdc  |
| Collector-Base Voltage                         | VCBO             | 50          | Vdc  |
| Emitter-Base Voltage                           | V <sub>EBO</sub> | 5.0         | Vdc  |
| Collector Current                              | IC               | 100         | mAdc |
| Total Device Dissipation T <sub>A</sub> =25 °C | PD               | 0.4         | W    |
| Junction Temperature                           | Tj               | 150         | °C   |
| Storage, Temperature                           | Tstg             | -55 to +150 | °C   |

#### **ELECTRICAL CHARACTERISTICS**

| Characteristics  | Symbol                | Min | Max | Unit |
|--|-----------------------|-----|-----|------|
| Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 0.1 mAdc, I <sub>B</sub> =0) | V <sub>(BR)</sub> CEO | 45  | -   | Vdc  |
| Collector-Base Breakdown Voltage (I <sub>C</sub> = 100uAdc, I <sub>B</sub> =0)     | V <sub>(BR)</sub> CBO | 50  | 1   | Vdc  |
| Emitter-Base Breakdown Voltage (I <sub>E</sub> = 100 uAdc, I <sub>C</sub> =0)      | V <sub>(BR)EBO</sub>  | 5.0 | -   | Vdc  |
| Collector Cutoff Current (VCB= 50 Vdc, IE=0)                                       | ICBO                  | -   | 0.1 | uAdc |
| Emitter Cutoff Current (V <sub>EB</sub> = 3.0Vdc, I <sub>C</sub> =0)               | I <sub>EBO</sub>      | -   | 0.1 | uAdc |

# S9014



## **Electrical Characteristics** (TA=25 °C unless otherwise noted) (Countinued)

| Characteristics | Symbol | Min | Max | Unit |
|-----------------|--------|-----|-----|------|
|-----------------|--------|-----|-----|------|

### **On Characteristics**

| DC Current Gain<br>S(Ic±1mAdc, VcE=5Vdc)  | HFE                  | 60  | 1000 | -   |
|---|----------------------|-----|------|-----|
| Collector-Emitter Saturation Voltage (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 5 mAdc) | VCE(sat)             | -   | 0.3  | Vdc |
| Base-Emitter Saturation Voltage (IC= 100 mAdc, IB= 5 mAdc)                                | V <sub>BE(sat)</sub> | ı   | 1    | Vdc |
| Transition Frequency (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 5 Vdc, f=30MHz)         | fT                   | 150 | -    | MHz |

#### CLASSIFICATION OF hFE

| Rank  | А      | В       | С       | D        |
|-------|--------|---------|---------|----------|
| Range | 60-150 | 100-300 | 200-600 | 400-1000 |

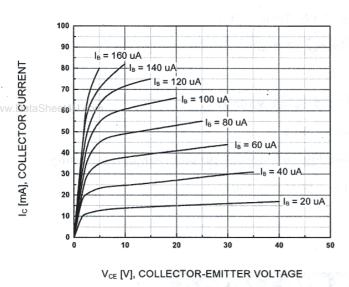


FIG.1 Static Characteristic

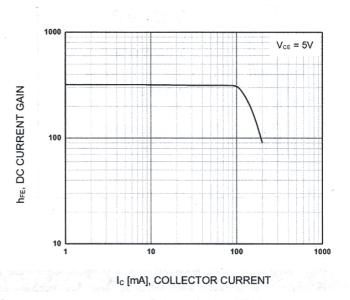


FIG.2 DC current Gain

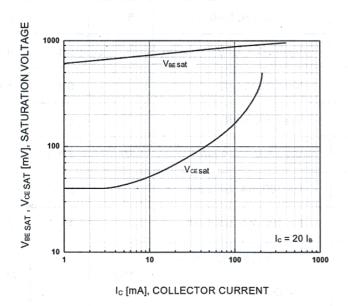


FIG.3 Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

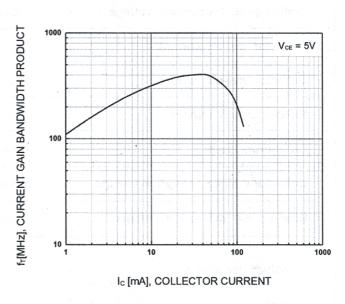
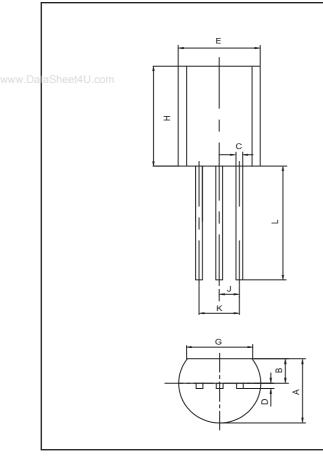


FIG.4 Current Gain Bandwidth Product



### **TO-92 Outline Dimensions**

unit:mm



| <b>TO-92</b> |          |       |  |  |
|--------------|----------|-------|--|--|
| Dim          | Min      | Max   |  |  |
| A            | 3.30     | 3.70  |  |  |
| В            | 1.10     | 1.40  |  |  |
| C            | 0.38     | 0.55  |  |  |
| D            | 0.36     | 0.51  |  |  |
| E            | 4.40     | 4.70  |  |  |
| G            | 3.43     | -     |  |  |
| H            | 4.30     | 4.70  |  |  |
| J            | 1.270TYP |       |  |  |
| K            | 2.44     | 2.64  |  |  |
| L            | 14.10    | 14.50 |  |  |